



Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	97
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000-1fg144t

I/Os Per Package

ProASIC3 Devices	A3P060	A3P125	A3P250		A3P1000	
Package	I/O Type					
	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O ²	Differential I/O Pairs	Single-Ended I/O ²	Differential I/O Pairs
VQ100	71	71	68	13	–	–
FG144	96	97	97	24	97	25
FG256	–	–	157	38	177	44
FG484	–	–	–	–	300	74
QNG132	–	84	87	19	–	–

Notes:

1. When considering migrating your design to a lower- or higher-density device, refer to the [ProASIC3 FPGA Fabric User's Guide](#) to ensure complying with design and board migration requirements.
2. Each used differential I/O pair reduces the number of available single-ended I/Os by two.
3. FG256 and FG484 are footprint-compatible packages.

Automotive ProASIC3 Device Status

Automotive ProASIC3 Devices	Status
A3P060	Production
A3P125	Production
A3P250	Production
A3P1000	Production

Calculating Power Dissipation

Quiescent Supply Current

Table 2-6 • Quiescent Supply Current Characteristics

	A3P060	A3P125	A3P250	A3P1000
Typical (25°C)	2 mA	2 mA	3 mA	8 mA
Maximum (Automotive Grade 1) – 135°C	53 mA	53 mA	106 mA	265 mA
Maximum (Automotive Grade 2) – 115°C	26 mA	26 mA	53 mA	131 mA

Note: I_{DD} includes V_{CC} , V_{PUMP} , V_{CCI} , and V_{MV} currents. Values do not include I/O static contribution, which is shown in Table 2-7 and Table 2-10 on page 2-8.

Power per I/O Pin

Table 2-7 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings ¹
Applicable to Advanced I/O Banks

	VMV (V)	Static Power PDC2 (mW) ¹	Dynamic Power PAC9 (μW/MHz) ²
Single-Ended			
3.3 V LVTTTL / 3.3 V LVCMOS	3.3	–	16.69
2.5 V LVCMOS	2.5	–	5.12
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.45
3.3 V PCI	3.3	–	18.11
3.3 V PCI-X	3.3	–	18.11
Differential			
LVDS	2.5	2.26	1.20
LVPECL	3.3	5.72	1.87

Notes:

- P_{DC2} is the static power (where applicable) measured on VMV.
- P_{AC9} is the total dynamic power measured on V_{CC} and VMV.

Table 2-10 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings ¹
Applicable to Standard Plus I/O Banks

	C _{LOAD} (pF)	V _{CCI} (V)	Static Power PDC3 (mW) ²	Dynamic Power PAC10 (μW/MHz) ³
Single-Ended				
3.3 V LVTTTL / 3.3 V LVCMOS	35	3.3	–	452.67
2.5 V LVCMOS	35	2.5	–	258.32
1.8 V LVCMOS	35	1.8	–	133.59
1.5 V LVCMOS (JESD8-11)	35	1.5	–	92.84
3.3 V PCI	10	3.3	–	184.92
3.3 V PCI-X	10	3.3	–	184.92

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. PDC3 is the static power (where applicable) measured on VMV.
3. PAC10 is the total dynamic power measured on VCCI and VMV.

I/O Output Buffer Contribution— P_{OUTPUTS}

$$P_{\text{OUTPUTS}} = N_{\text{OUTPUTS}} * \alpha_2 / 2 * \beta_1 * PAC10 * F_{\text{CLK}}$$

N_{OUTPUTS} is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-12.

β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-13 on page 2-12.

F_{CLK} is the global clock signal frequency.

RAM Contribution— P_{MEMORY}

$$P_{\text{MEMORY}} = PAC11 * N_{\text{BLOCKS}} * F_{\text{READ-CLOCK}} * \beta_2 + PAC12 * N_{\text{BLOCK}} * F_{\text{WRITE-CLOCK}} * \beta_3$$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{\text{READ-CLOCK}}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations.

$F_{\text{WRITE-CLOCK}}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in Table 2-13 on page 2-12.

PLL Contribution— P_{PLL}

$$P_{\text{PLL}} = PAC13 + PAC14 * F_{\text{CLKOUT}}$$

F_{CLKIN} is the input clock frequency.

F_{CLKOUT} is the output clock frequency.¹

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = (100% + 50% + 25% + 12.5% + . . . + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-12 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

1. The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($PAC14 * F_{\text{CLKOUT}}$ product) to the total PLL contribution.

Table 2-29 • I/O Short Currents I_{OSH}/I_{OSL}
Applicable to Standard Plus I/O Banks

	Drive Strength	I _{OSL} (mA)*	I _{OSH} (mA)*
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	27	25
	4 mA	27	25
	6 mA	54	51
	8 mA	54	51
	12 mA	109	103
	16 mA	109	103
2.5 V LVCMOS	2 mA	18	16
	6 mA	37	32
	12 mA	74	65
1.8 V LVCMOS	2 mA	11	9
	4 mA	22	17
	6 mA	44	35
	8 mA	44	35
1.5 V LVCMOS	2 mA	16	13
	4 mA	33	25
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	109	103

Note: *T_J = 100°C

The length of time an I/O can withstand I_{OSH}/I_{OSL} events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

For example, at 110°C, the short current condition would have to be sustained for more than three months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

Table 2-30 • Duration of Short Circuit Event before Failure

Temperature	Time before Failure
–40°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months
110°C	3 months
125°C	25 days
135°	12 days

Timing Characteristics

Table 2-46 • 2.5 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	9.69	0.05	1.45	0.46	8.76	9.69	1.48	1.25	11.26	12.187	ns
	-1	0.55	8.24	0.04	1.23	0.39	7.45	8.24	1.48	1.25	9.58	10.367	ns
6 mA	STD	0.64	5.78	0.05	1.45	0.46	5.63	5.78	1.68	1.62	8.13	8.277	ns
	-1	0.55	4.91	0.04	1.23	0.39	4.79	4.91	1.69	1.63	6.92	7.04	ns
12 mA	STD	0.64	3.98	0.05	1.45	0.46	4.05	3.84	1.82	1.86	6.55	6.338	ns
	-1	0.55	3.39	0.04	1.23	0.39	3.45	3.27	1.83	1.86	5.58	5.392	ns
16 mA	STD	0.64	3.75	0.05	1.45	0.46	1.85	1.69	3.76	3.97	3.06	2.926	ns
	-1	0.55	3.19	0.04	1.23	0.39	1.85	1.69	3.20	3.38	3.06	2.929	ns
24 mA	STD	0.64	3.45	0.05	1.45	0.46	1.70	1.35	3.84	4.47	2.92	2.585	ns
	-1	0.55	2.94	0.04	1.23	0.39	1.71	1.35	3.27	3.80	2.92	2.586	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-47 • 2.5 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	12.12	0.05	1.45	0.46	12.54	12.74	1.48	1.19	15.04	15.243	ns
	-1	0.55	10.31	0.04	1.23	0.39	10.67	10.84	1.48	1.20	12.80	12.966	ns
6 mA	STD	0.64	8.24	0.05	1.45	0.46	9.07	8.74	1.68	1.57	11.57	11.237	ns
	-1	0.55	7.01	0.04	1.23	0.39	7.71	7.43	1.69	1.57	9.84	9.559	ns
12 mA	STD	0.64	6.91	0.05	1.45	0.46	7.04	6.62	1.82	1.80	9.54	9.117	ns
	-1	0.55	5.88	0.04	1.23	0.39	5.99	5.63	1.83	1.80	8.11	7.756	ns
16 mA	STD	0.64	6.44	0.05	1.45	0.46	6.56	6.18	1.86	1.86	9.06	8.678	ns
	-1	0.55	5.48	0.04	1.23	0.39	5.58	5.26	1.86	1.86	7.71	7.382	ns
24 mA	STD	0.64	6.16	0.05	1.45	0.46	6.15	6.16	1.90	2.10	8.65	8.657	ns
	-1	0.55	5.24	0.04	1.23	0.39	5.23	5.24	1.90	2.10	7.36	7.364	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-50 • 2.5 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	9.37	0.05	1.40	0.45	8.47	9.37	1.43	1.21	10.89	11.79	ns
	-1	0.53	7.97	0.04	1.19	0.38	7.21	7.97	1.43	1.21	9.27	10.03	ns
6 mA	STD	0.63	5.59	0.05	1.40	0.45	5.45	5.59	1.63	1.57	7.87	8.01	ns
	-1	0.53	4.75	0.04	1.19	0.38	4.63	4.75	1.63	1.57	6.69	6.81	ns
12 mA	STD	0.63	3.85	0.05	1.40	0.45	3.92	3.71	1.77	1.80	6.34	6.13	ns
	-1	0.53	3.28	0.04	1.19	0.38	3.34	3.16	1.77	1.80	5.39	5.22	ns
16 mA	STD	0.63	3.63	0.05	1.40	0.45	1.79	1.64	3.64	3.84	2.96	2.83	ns
	-1	0.53	3.08	0.04	1.19	0.38	1.79	1.64	3.09	3.27	2.96	2.83	ns
24 mA	STD	0.63	3.34	0.05	1.40	0.45	1.65	1.31	3.72	4.32	2.82	2.50	ns
	-1	0.53	2.84	0.04	1.19	0.38	1.65	1.31	3.16	3.68	2.82	2.50	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-51 • 2.5 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	11.73	0.05	1.40	0.45	12.14	12.33	1.43	1.16	14.55	14.75	ns
	-1	0.53	9.98	0.04	1.19	0.38	10.32	10.49	1.43	1.16	12.38	12.55	ns
6 mA	STD	0.63	7.97	0.05	1.40	0.45	8.77	8.45	1.63	1.51	11.19	10.87	ns
	-1	0.53	6.78	0.04	1.19	0.38	7.46	7.19	1.63	1.52	9.52	9.25	ns
12 mA	STD	0.63	6.68	0.05	1.40	0.45	6.81	6.40	1.77	1.74	9.23	8.82	ns
	-1	0.53	5.69	0.04	1.19	0.38	5.79	5.45	1.77	1.74	7.85	7.50	ns
16 mA	STD	0.63	6.24	0.05	1.40	0.45	6.35	5.98	1.80	1.80	8.77	8.40	ns
	-1	0.53	5.30	0.04	1.19	0.38	5.40	5.08	1.80	1.80	7.46	7.14	ns
24 mA	STD	0.63	5.96	0.05	1.40	0.45	5.95	5.96	1.84	2.03	8.37	8.38	ns
	-1	0.53	5.07	0.04	1.19	0.38	5.06	5.07	1.84	2.03	7.12	7.12	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-54 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	I _{OL}	I _{OH}	I _{OSL}	I _{OSH}	I _{IL}	I _{IH}
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
2 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	2	2	11	9	10	10
4 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	4	4	22	17	10	10
6 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	6	6	44	35	10	10
8 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	8	8	51	45	10	10
12 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	12	12	74	91	10	10
16 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	16	16	74	91	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 125°C junction temperature.
3. Software default selection highlighted in gray.

Table 2-55 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	I _{OL}	I _{OH}	I _{OSL}	I _{OSH}	I _{IL}	I _{IH}
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
2 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	2	2	11	9	10	10
4 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	4	4	22	17	10	10
6 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	6	6	44	35	10	10
8 mA	−0.3	0.35 * V _{CCI}	0.65 * V _{CCI}	3.6	0.45	V _{CCI} − 0.45	8	8	44	35	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 125°C junction temperature.
3. Software default selection highlighted in gray.

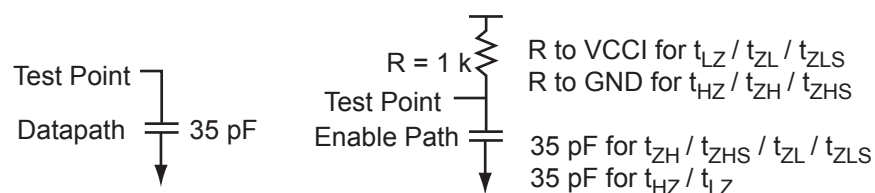


Figure 2-9 • AC Loading

Table 2-56 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.8	0.9	35

Note: *Measuring point = V_{trip}. See Table 2-18 on page 2-17 for a complete table of trip points.

Table 2-97 • Output Enable Register Propagation Delays
Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.53	0.62	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.37	0.44	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.52	0.61	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.79	0.93	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.79	0.93	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.27	0.31	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.27	0.31	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.25	0.30	ns
t_{OEWPPE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-100 • Input DDR Propagation Delays
Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{DDRICKQ1}	Clock-to-Out Out_QR for Input DDR	0.33	0.38	ns
t_{DDRICKQ2}	Clock-to-Out Out_QF for Input DDR	0.46	0.54	ns
t_{DDRISUD}	Data Setup for Input DDR	0.34	0.40	ns
t_{DDRILD}	Data Hold for Input DDR	0.00	0.00	ns
$t_{\text{DDRILR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.55	0.65	ns
$t_{\text{DDRILR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.68	0.80	ns
$t_{\text{DDRIREMCLR}}$	Asynchronous Clear Removal Time for Input DDR	0.00	0.00	ns
$t_{\text{DDRIRECCLR}}$	Asynchronous Clear Recovery Time for Input DDR	0.27	0.31	ns
$t_{\text{DDRILWCLR}}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.25	0.30	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.41	0.48	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.37	0.43	ns
F_{DDRIMAX}	Maximum Frequency for Input DDR	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-110 • A3P125 Global Resource
Commercial-Case Conditions: $T_J = 135^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.93	1.22	1.09	1.43	ns
t_{RCKH}	Input High Delay for Global Clock	0.92	1.26	1.08	1.49	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.80		0.94		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.98		1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.35		0.41	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-111 • A3P125 Global Resource
Commercial-Case Conditions: $T_J = 115^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.90	1.19	1.06	1.40	ns
t_{RCKH}	Input High Delay for Global Clock	0.90	1.23	1.05	1.45	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.80		0.94		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.98		1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.34		0.40	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-112 • A3P250 Global Resource
Commercial-Case Conditions: $T_J = 135^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.96	1.25	1.13	1.47	ns
t_{RCKH}	Input High Delay for Global Clock	0.94	1.28	1.10	1.51	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.80		0.94		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.98		1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.35		0.41	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-113 • A3P250 Global Resource
Commercial-Case Conditions: $T_J = 115^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.94	1.22	1.10	1.44	ns
t_{RCKH}	Input High Delay for Global Clock	0.92	1.25	1.08	1.47	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.80		0.94		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.98		1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.34		0.40	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the ["User I/O Characteristics" section on page 2-12](#) for more details.

Timing Characteristics

Table 2-125 • JTAG 1532

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DISU}	Test Data Input Setup Time				ns
t_{DIHD}	Test Data Input Hold Time				ns
t_{TMSSU}	Test Mode Select Setup Time				ns
t_{TMDHD}	Test Mode Select Hold Time				ns
t_{TCK2Q}	Clock to Q (data out)				ns
t_{RSTB2Q}	Reset to Q (data out)				ns
F_{TCKMAX}	TCK Maximum Frequency	20	20	20	MHz
t_{TRSTREM}	ResetB Removal Time				ns
t_{TRSTREC}	ResetB Recovery Time				ns
t_{TRSTMPW}	ResetB Minimum Pulse				ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

3 – Pin Descriptions and Packaging

Supply Pins

GND**Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ**Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC**Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx**I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to four I/O banks on Automotive ProASIC3 devices, plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VCCI pins tied to GND.

VMVx**I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. x is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F**PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V.

When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the [Automotive ProASIC3 FPGA Fabric User's Guide](#) for a complete board solution for the PLL analog power supply and ground.

There is one VCCPLF pin on Automotive ProASIC3 devices.

VCOMPLA/B/C/D/E/F**PLL Ground**

Ground to analog PLL power supplies. When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There is one VCOMPLF pin on Automotive ProASIC3 devices.

VJTAG**JTAG Supply Voltage**

Automotive ProASIC3 devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND. It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is

Special Function Pins

NC

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

No Connect

DC

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

Do Not Connect

Packaging

Semiconductor technology is constantly shrinking in size while growing in capability and functional integration. To enable next-generation silicon technologies, semiconductor packages have also evolved to provide improved performance and flexibility.

Microsemi consistently delivers packages that provide the necessary mechanical and environmental protection to ensure consistent reliability and performance. Microsemi IC packaging technology efficiently supports high-density FPGAs with large-pin-count Ball Grid Arrays (BGAs), but is also flexible enough to accommodate stringent form factor requirements for Chip Scale Packaging (CSP). In addition, Actel offers a variety of packages designed to meet your most demanding application and economic requirements for today's embedded and mobile systems.

Related Documents

User's Guides

Automotive ProASIC FPGA Fabric User's Guide

http://www.microsemi.com/soc/documents/PA3_Auto_UG.pdf

Packaging

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

Package Mechanical Drawings

<http://www.microsemi.com/soc/documents/PckgMechDrwngs.pdf>

This document contains the package mechanical drawings for all packages currently or previously supplied by Actel. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials: <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.

FG144	
Pin Number	A3P060 Function
K1	GEB0/IO74RSB1
K2	GEA1/IO73RSB1
K3	GEA0/IO72RSB1
K4	GEA2/IO71RSB1
K5	IO65RSB1
K6	IO64RSB1
K7	GND
K8	IO57RSB1
K9	GDC2/IO56RSB1
K10	GND
K11	GDA0/IO50RSB0
K12	GDB0/IO48RSB0
L1	GND
L2	VMV1
L3	GEB2/IO70RSB1
L4	IO67RSB1
L5	VCCIB1
L6	IO62RSB1
L7	IO59RSB1
L8	IO58RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO69RSB1
M3	IO68RSB1
M4	IO66RSB1
M5	IO63RSB1
M6	IO61RSB1
M7	IO60RSB1
M8	NC
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG256	
Pin Number	A3P1000 Function
G13	GCC1/IO91PPB1
G14	IO90NPB1
G15	IO88PDB1
G16	IO88NDB1
H1	GFB0/IO208NPB3
H2	GFA0/IO207NDB3
H3	GFB1/IO208PPB3
H4	VCOMPLF
H5	GFC0/IO209NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO91NPB1
H13	GCB1/IO92PPB1
H14	GCA0/IO93NPB1
H15	IO96NPB1
H16	GCB0/IO92NPB1
J1	GFA2/IO206PSB3
J2	GFA1/IO207PDB3
J3	VCCPLF
J4	IO205NDB3
J5	GFB2/IO205PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO95PPB1
J13	GCA1/IO93PPB1
J14	GCC2/IO96PPB1
J15	IO100PPB1
J16	GCA2/IO94PSB1

FG256	
Pin Number	A3P1000 Function
K1	GFC2/IO204PDB3
K2	IO204NDB3
K3	IO203NDB3
K4	IO203PDB3
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO95NPB1
K14	IO100NPB1
K15	IO102NDB1
K16	IO102PDB1
L1	IO202NDB3
L2	IO202PDB3
L3	IO196PPB3
L4	IO193PPB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO112NPB1
L14	IO106NDB1
L15	IO106PDB1
L16	IO107PDB1
M1	IO197NSB3
M2	IO196NPB3
M3	IO193NPB3
M4	GEC0/IO190NPB3

FG256	
Pin Number	A3P1000 Function
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO147RSB2
M9	IO136RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO110NDB1
M14	GDB1/IO112PPB1
M15	GDC1/IO111PDB1
M16	IO107NDB1
N1	IO194PSB3
N2	IO192PPB3
N3	GEC1/IO190PPB3
N4	IO192NPB3
N5	GNDQ
N6	GEA2/IO187RSB2
N7	IO161RSB2
N8	IO155RSB2
N9	IO141RSB2
N10	IO129RSB2
N11	IO124RSB2
N12	GNDQ
N13	IO110PDB1
N14	VJTAG
N15	GDC0/IO111NDB1
N16	GDA1/IO113PDB1
P1	GEB1/IO189PDB3
P2	GEB0/IO189NDB3
P3	VMV2
P4	IO179RSB2
P5	IO171RSB2
P6	IO165RSB2
P7	IO159RSB2
P8	IO151RSB2

FG256	
Pin Number	A3P1000 Function
P9	IO137RSB2
P10	IO134RSB2
P11	IO128RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO113NDB1
R1	GEA1/IO188PDB3
R2	GEA0/IO188NDB3
R3	IO184RSB2
R4	GEC2/IO185RSB2
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2

FG256	
Pin Number	A3P1000 Function
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

